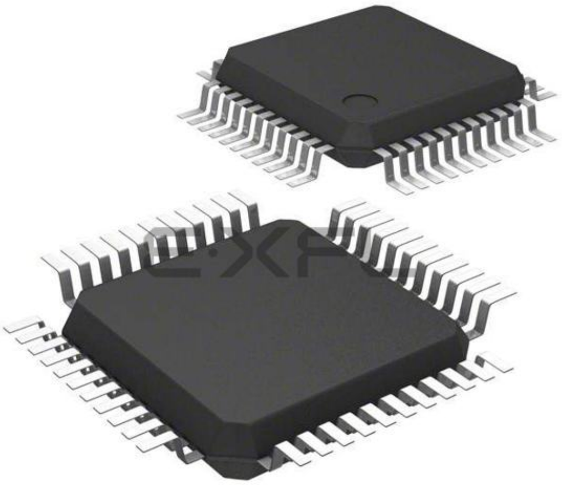

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

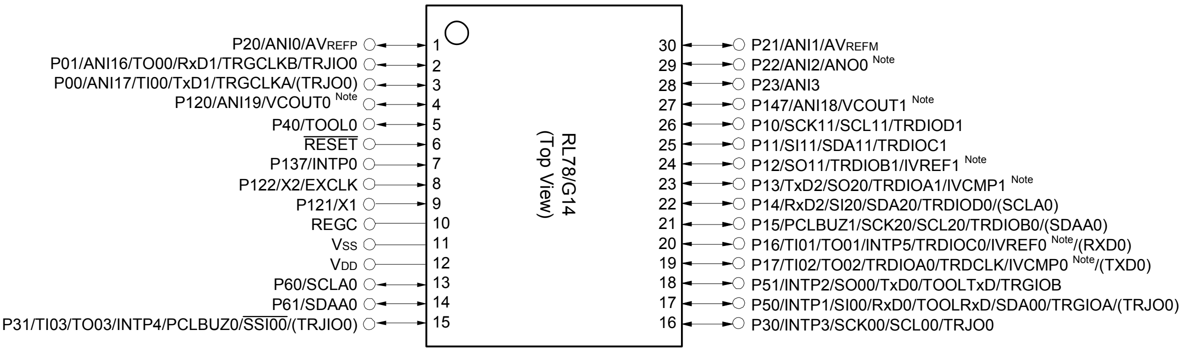
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104fgafp-30

1.3 Pin Configuration (Top View)

1.3.1 30-pin products

- 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



Note Mounted on the 96 KB or more code flash memory products.

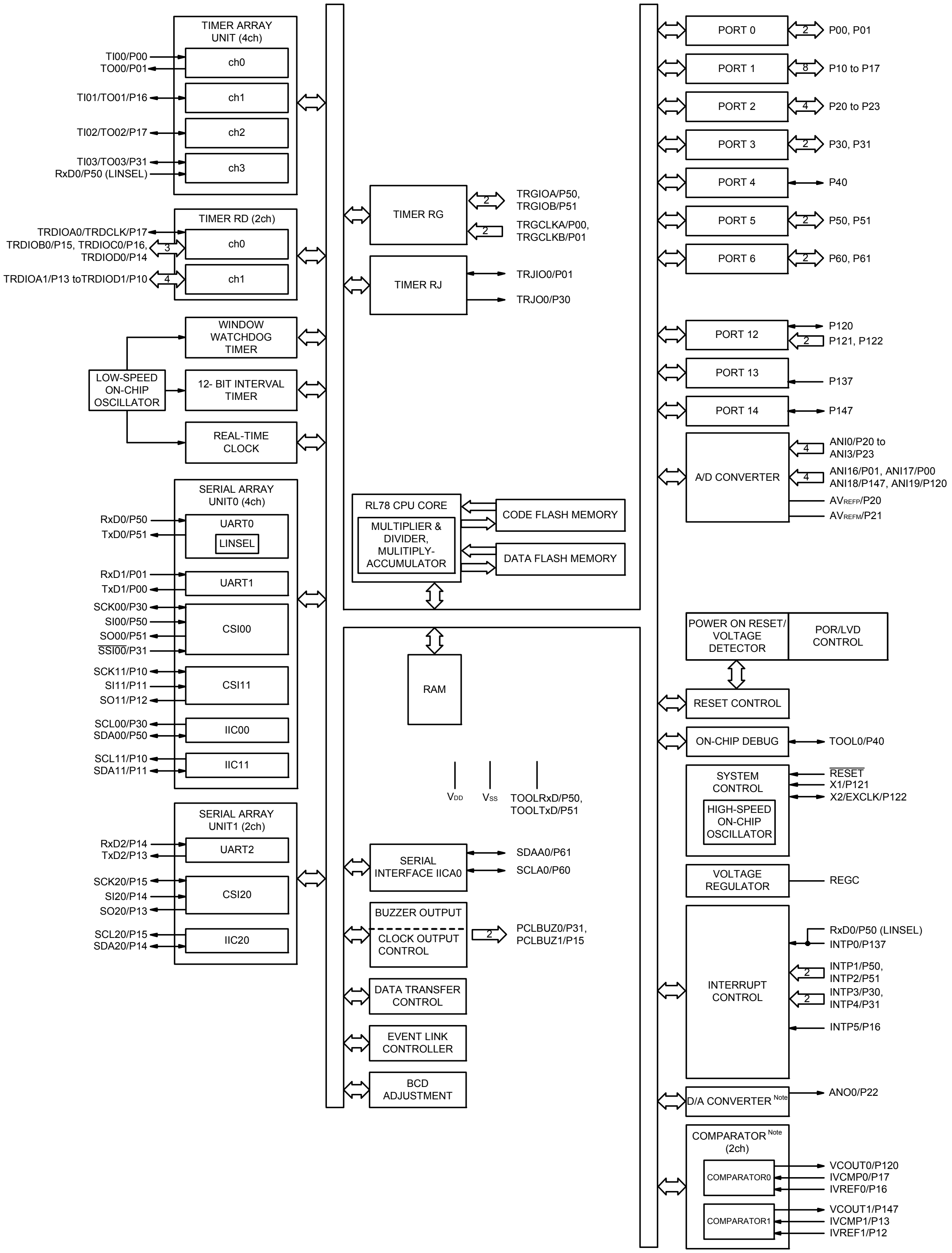
Caution Connect the REGC pin to V_{SS} pin via a capacitor (0.47 to 1 μF).

Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

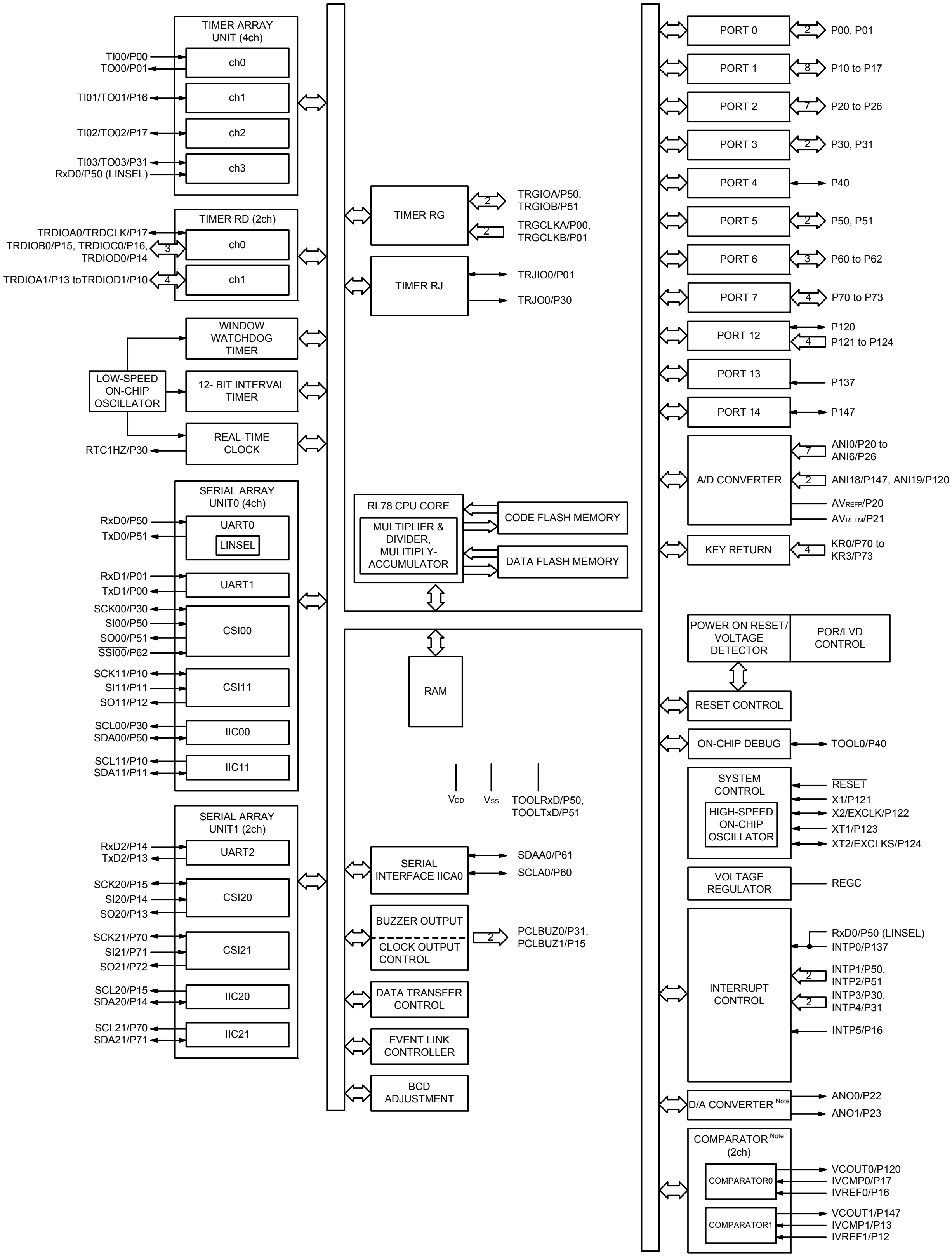
1.5 Block Diagram

1.5.1 30-pin products



Note Mounted on the 96 KB or more code flash memory products.

1.5.4 40-pin products



Note Mounted on the 96 KB or more code flash memory products.

(2/2)

Item		44-pin	48-pin	52-pin	64-pin
		R5F104Fx (x = A, C to E)	R5F104Gx (x = A, C to E)	R5F104Jx (x = C to E)	R5F104Lx (x = C to E)
Clock output/buzzer output		2	2	2	2
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation)			
8/10-bit resolution A/D converter		10 channels	10 channels	12 channels	12 channels
Serial interface		[44-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I^{2}C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^{2}C: 1 channel • CSI: 2 channels/UART: 1 channel/simplified I^{2}C: 2 channels [48-pin, 52-pin products] • CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I^{2}C: 2 channels • CSI: 1 channel/UART: 1 channel/simplified I^{2}C: 1 channel • CSI: 2 channels/UART: 1 channel/simplified I^{2}C: 2 channels [64-pin products] • CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I^{2}C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I^{2}C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I^{2}C: 2 channels			
	I^{2}C bus	1 channel	1 channel	1 channel	1 channel
Data transfer controller (DTC)		29 sources	30 sources		31 sources
Event link controller (ELC)		Event input: 20 Event trigger output: 7			
Vectored interrupt sources	Internal	24	24	24	24
	External	7	10	12	13
Key interrupt		4	6	8	8
Reset		• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution [Note] • Internal reset by RAM parity error • Internal reset by illegal-memory access			
Power-on-reset circuit		• Power-on-reset: 1.51 ±0.04 V (T_A = –40 to +85°C) 1.51 ±0.06 V (T_A = –40 to +105°C) • Power-down-reset: 1.50 ±0.04 V (T_A = –40 to +85°C) 1.50 ±0.06 V (T_A = –40 to +105°C)			
Voltage detector		1.63 V to 4.06 V (14 stages)			
On-chip debug function		Provided			
Power supply voltage		V_{DD} = 1.6 to 5.5 V (T_A = -40 to +85°C) V_{DD} = 2.4 to 5.5 V (T_A = -40 to +105°C)			
Operating ambient temperature		T_A = –40 to +85°C (A: Consumer applications, D: Industrial applications), T_A = -40 to +105°C (G: Industrial applications)			

Note The illegal instruction is generated when instruction code FFH is executed.
Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

(2/2)

Item		80-pin	100-pin
		R5F104Mx (x = F to H, J)	R5F104Px (x = F to H, J)
Clock output/buzzer output		2	2
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation)	
8/10-bit resolution A/D converter		17 channels	20 channels
D/A converter		2 channels	2 channels
Comparator		2 channels	2 channels
Serial interface		[80-pin, 100-pin products] • CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I^{2}C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I^{2}C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I^{2}C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I^{2}C: 2 channels	
	I^{2}C bus	2 channels	2 channels
Data transfer controller (DTC)		39 sources	39 sources
Event link controller (ELC)		Event input: 26 Event trigger output: 9	
Vectored interrupt sources	Internal	32	32
	External	13	13
Key interrupt		8	8
Reset		• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution [Note] • Internal reset by RAM parity error • Internal reset by illegal-memory access	
Power-on-reset circuit		• Power-on-reset: 1.51 ±0.04 V (T_A = –40 to +85°C) 1.51 ±0.06 V (T_A = –40 to +105°C) • Power-down-reset: 1.50 ±0.04 V (T_A = –40 to +85°C) 1.50 ±0.06 V (T_A = –40 to +105°C)	
Voltage detector		1.63 V to 4.06 V (14 stages)	
On-chip debug function		Provided	
Power supply voltage		V_{DD} = 1.6 to 5.5 V (T_A = -40 to +85°C) V_{DD} = 2.4 to 5.5 V (T_A = -40 to +105°C)	
Operating ambient temperature		T_A = -40 to +85°C (A: Consumer applications, D: Industrial applications), T_A = -40 to +105°C (G: Industrial applications)	

Note The illegal instruction is generated when instruction code FFH is executed.
Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2.3 DC Characteristics

2.3.1 Pin characteristics

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	I_{OH1}	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	1.6 V ≤ EV_{DD0} ≤ 5.5 V			-10.0 Note 2	mA
		Total of P00 to P04, P40 to P47, P102, P120, P130, P140 to P145 (When duty ≤ 70% Note 3)	4.0 V ≤ EV_{DD0} ≤ 5.5 V			-55.0	mA
			2.7 V ≤ EV_{DD0} < 4.0 V			-10.0	mA
			1.8 V ≤ EV_{DD0} < 2.7 V			-5.0	mA
			1.6 V ≤ EV_{DD0} < 1.8 V			-2.5	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147 (When duty ≤ 70% Note 3)	4.0 V ≤ EV_{DD0} ≤ 5.5 V			-80.0	mA
			2.7 V ≤ EV_{DD0} < 4.0 V			-19.0	mA
			1.8 V ≤ EV_{DD0} < 2.7 V			-10.0	mA
			1.6 V ≤ EV_{DD0} < 1.8 V			-5.0	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ EV_{DD0} ≤ 5.5 V			-135.0 Note 4	mA
	I_{OH2}	Per pin for P20 to P27, P150 to P156	1.6 V ≤ V_{DD} ≤ 5.5 V			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ V_{DD} ≤ 5.5 V			-1.5	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%.
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)
  <Example> Where n = 80% and I_{OH} = -10.0 mA
  Total output current of pins = (-10.0 × 0.7)/(80 × 0.01) ≈ -8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.
A current higher than the absolute maximum rating must not flow into one pin.

Note 4. -100 mA for industrial applications (R5F104xxDxx, R5F104xxGxx).

Caution **P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 do not output high level in N-ch open-drain mode.**

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

(T_A = -40 to +85°C, 1.6 V $\le$ EV_{DD0} $\le$ V_{DD} $\le$ 5.5 V, V_{SS} = EV_{SS0} = 0 V)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode Note 5	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 3	Basic operation	V_{DD} = 5.0 V		2.4		mA
						V_{DD} = 3.0 V		2.4		
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 3	Basic operation	V_{DD} = 5.0 V		2.1		
						V_{DD} = 3.0 V		2.1		
			HS (high-speed main) mode Note 5	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 3	Normal operation	V_{DD} = 5.0 V		5.1	8.7	mA
						V_{DD} = 3.0 V		5.1	8.7	
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 3	Normal operation	V_{DD} = 5.0 V		4.8	8.1	
						V_{DD} = 3.0 V		4.8	8.1	
				f_{HOCO} = 48 MHz, f_{IH} = 24 MHz Note 3	Normal operation	V_{DD} = 5.0 V		4.0	6.9	
						V_{DD} = 3.0 V		4.0	6.9	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz Note 3	Normal operation	V_{DD} = 5.0 V		3.8	6.3	
						V_{DD} = 3.0 V		3.8	6.3	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz Note 3	Normal operation	V_{DD} = 5.0 V		2.8	4.6	
						V_{DD} = 3.0 V		2.8	4.6	
			LS (low-speed main) mode Note 5	f_{HOCO} = 8 MHz, f_{IH} = 8 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.3	2.0	mA
						V_{DD} = 2.0 V		1.3	2.0	
			LV (low-voltage main) mode Note 5	f_{HOCO} = 4 MHz, f_{IH} = 4 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.3	1.8	mA
						V_{DD} = 2.0 V		1.3	1.8	
			HS (high-speed main) mode Note 5	f_{MX} = 20 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		3.3	5.3	mA
						Resonator connection		3.4	5.5	
				f_{MX} = 20 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		3.3	5.3	
						Resonator connection		3.4	5.5	
				f_{MX} = 10 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		2.0	3.1	
						Resonator connection		2.1	3.2	
				f_{MX} = 10 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		2.0	3.1	
						Resonator connection		2.1	3.2	
			LS (low-speed main) mode Note 5	f_{MX} = 8 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		1.2	1.9	mA
						Resonator connection		1.2	2.0	
				f_{MX} = 8 MHz Note 2, V_{DD} = 2.0 V	Normal operation	Square wave input		1.2	1.9	
						Resonator connection		1.2	2.0	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 4 T_A = -40°C	Normal operation	Square wave input		4.7	6.1	μA
						Resonator connection		4.7	6.1	
				f_{SUB} = 32.768 kHz Note 4 T_A = +25°C	Normal operation	Square wave input		4.7	6.1	
						Resonator connection		4.7	6.1	
				f_{SUB} = 32.768 kHz Note 4 T_A = +50°C	Normal operation	Square wave input		4.8	6.7	
						Resonator connection		4.8	6.7	
				f_{SUB} = 32.768 kHz Note 4 T_A = +70°C	Normal operation	Square wave input		4.8	7.5	
						Resonator connection		4.8	7.5	
				f_{SUB} = 32.768 kHz Note 4 T_A = +85°C	Normal operation	Square wave input		5.4	8.9	
						Resonator connection		5.4	8.9	

(**Notes** and **Remarks** are listed on the next page.)

Note 1. Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 3. When high-speed system clock and subsystem clock are stopped.

Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.

Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$@1 MHz to 32 MHz
$2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$@1 MHz to 16 MHz
LS (low-speed main) mode: $1.8 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$@1 MHz to 8 MHz
LV (low-voltage main) mode: $1.6 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$@1 MHz to 4 MHz

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (64 MHz max.)
Remark 3. f_{IH}: High-speed on-chip oscillator clock frequency (32 MHz max.)
Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)
Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

Note 1. Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. During HALT instruction execution by flash memory.

Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 4. When high-speed system clock and subsystem clock are stopped.

Note 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.

Note 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.

Note 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz
2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (64 MHz max.)

Remark 3. f_{IH}: High-speed on-chip oscillator clock frequency (32 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)
(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ $4/f_{CLK}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V	125		500		1000		ns
			2.4 V ≤ EV_{DD0} ≤ 5.5 V	250		500		1000		ns
			1.8 V ≤ EV_{DD0} ≤ 5.5 V	500		500		1000		ns
			1.7 V ≤ EV_{DD0} ≤ 5.5 V	1000		1000		1000		ns
			1.6 V ≤ EV_{DD0} ≤ 5.5 V	—		1000		1000		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V		$t_{KCY1}/2$ - 12		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		ns
		2.7 V ≤ EV_{DD0} ≤ 5.5 V		$t_{KCY1}/2$ - 18		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V		$t_{KCY1}/2$ - 38		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		ns
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		ns
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		$t_{KCY1}/2$ - 100		$t_{KCY1}/2$ - 100		$t_{KCY1}/2$ - 100		ns
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		$t_{KCY1}/2$ - 100		$t_{KCY1}/2$ - 100		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V		44		110		110		ns
		2.7 V ≤ EV_{DD0} ≤ 5.5 V		44		110		110		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V		75		110		110		ns
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		110		110		110		ns
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		220		220		220		ns
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		220		220		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}	1.7 V ≤ EV_{DD0} ≤ 5.5 V		19		19		19		ns
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		19		19		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	1.7 V ≤ EV_{DD0} ≤ 5.5 V C = 30 pF Note 4			25		25		25	ns
		1.6 V ≤ EV_{DD0} ≤ 5.5 V C = 30 pF Note 4			—		25		25	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution **Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00 to 03, 10 to 13))

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions			HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		transmission	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V			Note 1		Note 1		Note 1	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V			Note 3		Note 3		Note 3	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps

Note 1. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD0} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to **Note 1** above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ EV_{DD0} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85°C, 2.7 V $\leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq$ 5.5 V, $V_{SS} = EV_{SS0} = EV_{SS1}$ = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 2/f_{CLK}$	4.0 V $\leq EV_{DD0} \leq$ 5.5 V, 2.7 V $\leq V_b \leq$ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ	200		1150		1150		ns
			2.7 V $\leq EV_{DD0} <$ 4.0 V, 2.3 V $\leq V_b \leq$ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	300		1150		1150		ns
SCKp high-level width	t_{KH1}	4.0 V $\leq EV_{DD0} \leq$ 5.5 V, 2.7 V $\leq V_b \leq$ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		ns
		2.7 V $\leq EV_{DD0} <$ 4.0 V, 2.3 V $\leq V_b \leq$ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		$t_{KCY1}/2$ - 120		$t_{KCY1}/2$ - 120		$t_{KCY1}/2$ - 120		ns
SCKp low-level width	t_{KL1}	4.0 V $\leq EV_{DD0} \leq$ 5.5 V, 2.7 V $\leq V_b \leq$ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		$t_{KCY1}/2$ - 7		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		ns
		2.7 V $\leq EV_{DD0} <$ 4.0 V, 2.3 V $\leq V_b \leq$ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		$t_{KCY1}/2$ - 10		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V $\leq EV_{DD0} \leq$ 5.5 V, 2.7 V $\leq V_b \leq$ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		58		479		479		ns
		2.7 V $\leq EV_{DD0} <$ 4.0 V, 2.3 V $\leq V_b \leq$ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		121		479		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	4.0 V $\leq EV_{DD0} \leq$ 5.5 V, 2.7 V $\leq V_b \leq$ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		10		ns
		2.7 V $\leq EV_{DD0} <$ 4.0 V, 2.3 V $\leq V_b \leq$ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	4.0 V $\leq EV_{DD0} \leq$ 5.5 V, 2.7 V $\leq V_b \leq$ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ			60		60		60	ns
		2.7 V $\leq EV_{DD0} <$ 4.0 V, 2.3 V $\leq V_b \leq$ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			130		130		130	ns

(**Notes**, **Caution**, and **Remarks** are listed on the next page.)

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI14, ANI16 to ANI20

(T_A = -40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, 1.6 V ≤ EV_{DD} = EV_{DD1} ≤ V_{DD}, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{BGR} Note 3, Reference voltage (-) = AV_{REFM} = 0 V Note 4, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8			bit
Conversion time	t_{CONV}	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	µs
Zero-scale error Notes 1, 2	E_{ZS}	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	% FSR
Integral linearity error Note 1	ILE	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±1.0	LSB
Analog input voltage	V_{AIN}			0		V_{BGR} Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to **2.6.2 Temperature sensor characteristics/internal reference voltage characteristic**.

Note 4. When reference voltage (-) = V_{SS}, the MAX. values are as follows.

Zero-scale error:	Add ±0.35%FSR to the MAX. value when reference voltage (-) = AV_{REFM}.
Integral linearity error:	Add ±0.5 LSB to the MAX. value when reference voltage (-) = AV_{REFM}.
Differential linearity error:	Add ±0.2 LSB to the MAX. value when reference voltage (-) = AV_{REFM}.

Note 1. Total current flowing into V_{DD} and EV_{DD0}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0} or V_{SS}, EV_{SS0}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 3. When high-speed system clock and subsystem clock are stopped.

Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.

Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7\ V \leq V_{DD} \leq 5.5\ V$@1 MHz to 32 MHz

$2.4\ V \leq V_{DD} \leq 5.5\ V$@1 MHz to 16 MHz

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (64 MHz max.)

Remark 3. f_{IH}: High-speed on-chip oscillator clock frequency (32 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

<R>

(3) Flash ROM: 384 to 512 KB of 48- to 100-pin products

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.93	5.16	mA
					V_{DD} = 3.0 V		0.93	5.16	
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.5	4.47	
					V_{DD} = 3.0 V		0.5	4.47	
				f_{HOCO} = 48 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.72	4.08	
					V_{DD} = 3.0 V		0.72	4.08	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.42	3.51	
					V_{DD} = 3.0 V		0.42	3.51	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		0.39	2.38	
					V_{DD} = 3.0 V		0.39	2.38	
			HS (high-speed main) mode Note 7	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.31	2.83	mA
					Resonator connection		0.41	2.92	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.31	2.83	
					Resonator connection		0.41	2.92	
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.21	1.46	
					Resonator connection		0.26	1.57	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.21	1.46	
					Resonator connection		0.26	1.57	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5, T_A = -40°C	Square wave input		0.31	0.76	μA
					Resonator connection		0.50	0.95	
				f_{SUB} = 32.768 kHz Note 5, T_A = +25°C	Square wave input		0.38	0.76	
					Resonator connection		0.57	0.95	
				f_{SUB} = 32.768 kHz Note 5, T_A = +50°C	Square wave input		0.47	3.59	
					Resonator connection		0.70	3.78	
				f_{SUB} = 32.768 kHz Note 5, T_A = +70°C	Square wave input		0.80	6.20	
					Resonator connection		1.00	6.39	
				f_{SUB} = 32.768 kHz Note 5, T_A = +85°C	Square wave input		1.65	10.56	
					Resonator connection		1.84	10.75	
				f_{SUB} = 32.768 kHz Note 5, T_A = +105°C	Square wave input		8.00	65.7	
					Resonator connection		8.00	65.7	
	I_{DD3} Note 6	STOP mode Note 8	T_A = -40°C				0.19	0.63	μA
			T_A = +25°C				0.30	0.63	
			T_A = +50°C				0.41	3.47	
			T_A = +70°C				0.80	6.08	
			T_A = +85°C				1.53	10.44	
			T_A = +105°C				6.50	67.14	

(**Notes** and **Remarks** are listed on the next page.)

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit
				MIN.	MAX.	
SCKp cycle time Note 5	t_{KCY2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V	20 MHz < f_{MCK}	16/f_{MCK}		ns
			f_{MCK} ≤ 20 MHz	12/f_{MCK}		ns
		2.7 V ≤ EV_{DD0} ≤ 5.5 V	16 MHz < f_{MCK}	16/f_{MCK}		ns
			f_{MCK} ≤ 16 MHz	12/f_{MCK}		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V		12/f_{MCK} and 1000		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V		t_{KCY2}/2 - 14		ns
		2.7 V ≤ EV_{DD0} ≤ 5.5 V		t_{KCY2}/2 - 16		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V		t_{KCY2}/2 - 36		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ EV_{DD0} ≤ 5.5 V		1/f_{MCK} + 40		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V		1/f_{MCK} + 60		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI2}			1/f_{MCK} + 62		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note 4	2.7 V ≤ EV_{DD0} ≤ 5.5 V		2/f_{MCK} + 66	ns
			2.4 V ≤ EV_{DD0} ≤ 5.5 V		2/f_{MCK} + 113	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution **Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1),
n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00 to 03, 10 to 13))

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
Data setup time (reception)	$t_{SU:DAT}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	$1/f_{MCK} + 340$ $^{\text{Note 2}}$		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	$1/f_{MCK} + 340$ $^{\text{Note 2}}$		ns
		4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	$1/f_{MCK} + 760$ $^{\text{Note 2}}$		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	$1/f_{MCK} + 760$ $^{\text{Note 2}}$		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	$1/f_{MCK} + 570$ $^{\text{Note 2}}$		ns
Data hold time (transmission)	$t_{HD:DAT}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	0	770	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	0	770	ns
		4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	0	1420	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	1420	ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	0	1215	ns

Note 1. The value must also be equal to or less than $f_{MCK}/4$.

Note 2. Set the f_{MCK} value to keep the hold time of SCLr = “L” and SCLr = “H”.

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

(2) Interrupt & Reset Mode

(T_A = -40 to +105°C, $V_{PDR} \leq V_{DD} \leq 5.5$ V, V_{SS} = 0 V)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Voltage detection threshold	V_{LVDD0}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 1, 1, falling reset voltage			2.64	2.75	2.86	V
	V_{LVDD1}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
				Falling interrupt voltage	2.75	2.86	2.97	V
	V_{LVDD2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
				Falling interrupt voltage	2.85	2.96	3.07	V
	V_{LVDD3}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
				Falling interrupt voltage	3.83	3.98	4.13	V

3.6.7 Power supply voltage rising slope characteristics

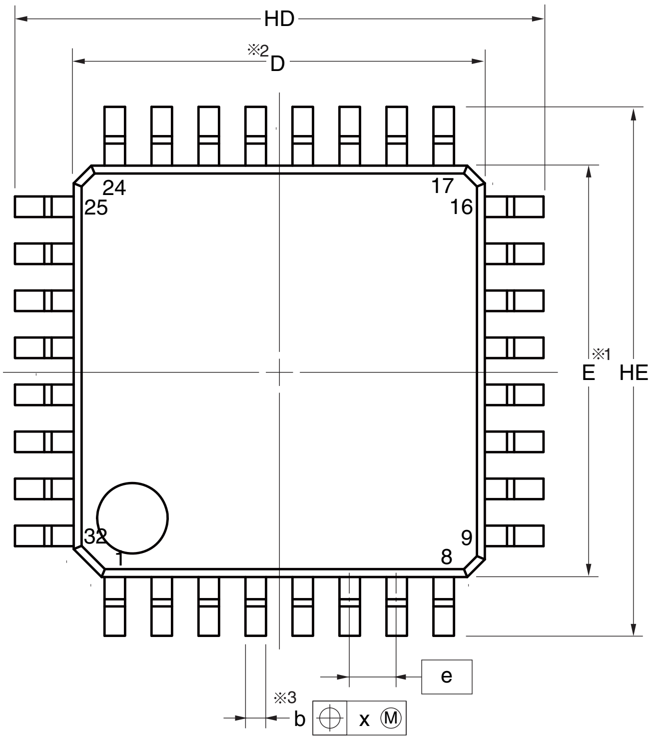
(T_A = -40 to +105°C, V_{SS} = 0 V)

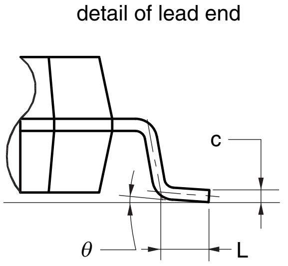
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

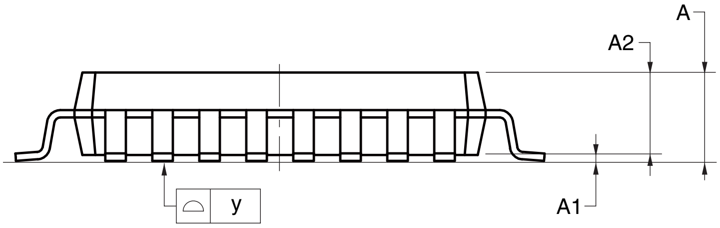
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

R5F104BAAFP, R5F104BCAFP, R5F104BDAFP, R5F104BEAFP, R5F104BFAFP, R5F104BGAFP
R5F104BADFP, R5F104BCDFP, R5F104BDDFP, R5F104BEDFP, R5F104BFDFP, R5F104BGDFP
R5F104BAGFP, R5F104BCGFP, R5F104BDGFP, R5F104BEGFP, R5F104BFGFP, R5F104BGGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2







(UNIT:mm)

ITEM	DIMENSIONS
D	7.00±0.10
E	7.00±0.10
HD	9.00±0.20
HE	9.00±0.20
A	1.70 MAX.
A1	0.10±0.10
A2	1.40
b	0.37±0.05
c	0.145±0.055
L	0.50±0.20
θ	0° to 8°
e	0.80
x	0.20
y	0.10

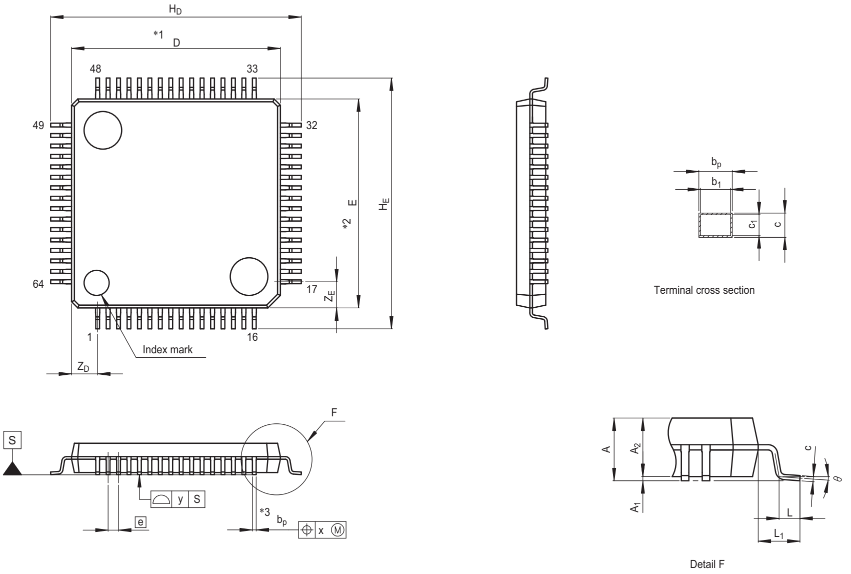
NOTE

1.Dimensions “※1” and “※2” do not include mold flash.

2.Dimension “※3” does not include trim offset.

R5F104LKAFB, R5F104LLAFB
R5F104LKGFB, R5F104LLGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LFQFP64-10x10-0.50	PLQP0064KB-A	64P6Q-A / FP-64K / FP-64KV	0.3g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	9.9	10.0	10.1
E	9.9	10.0	10.1
A_2	—	1.4	—
H_D	11.8	12.0	12.2
H_E	11.8	12.0	12.2
A	—	—	1.7
A_1	0.05	0.1	0.15
b_p	0.15	0.20	0.25
b_1	—	0.18	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
$\boxed{e}$	—	0.5	—
x	—	—	0.08
y	—	—	0.08
Z_D	—	1.25	—
Z_E	—	1.25	—
L	0.35	0.5	0.65
L_1	—	1.0	—